

GSDSB5819WS

Schottky Barrier Rectifier

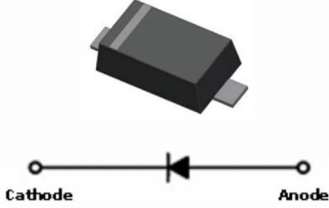
Product Description

Schottky Barrier Diodes 250mW / 40V

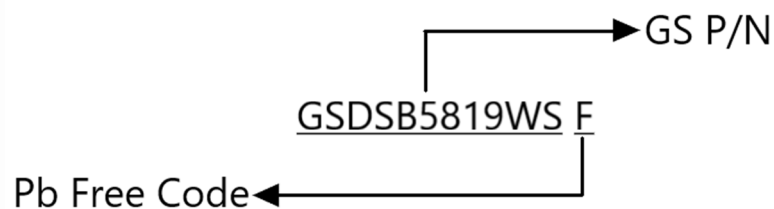
Features

- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicates Cathode
- Weight: approx.0.004g

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit Diagram
GSDSB5819WSF	SOD-323	SL	

Ordering Information



Part Number	Package	Quantity
GSDSB5819WSF	SOD-323	3,000 PCS

Absolute Maximum Ratings

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
P _D	Power Dissipation	250	mW
V _{RM}	Repetitive Peak Reverse Voltage	40	V
T _J	Operating Junction Temperature	+125	°C
T _{STG}	Storage Temperature Range	-55 to +125	°C
I _O	Average Rectified Output Current	1	A
I _{FSM}	Forward current surge peak (t=8.3ms Single Half Sine-wave)	9	A
I _{FRM}	Repetitive Peak Forward Current	1.5	A

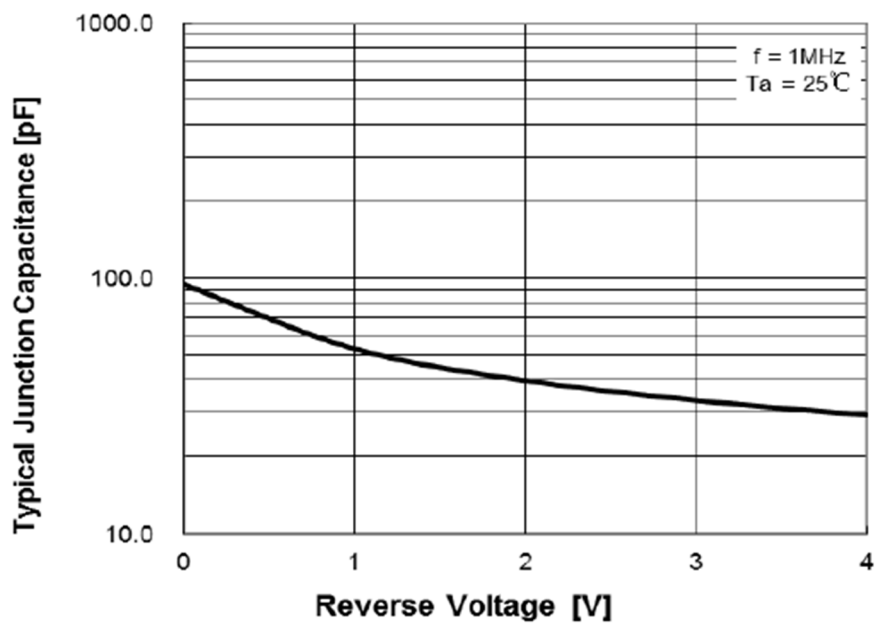
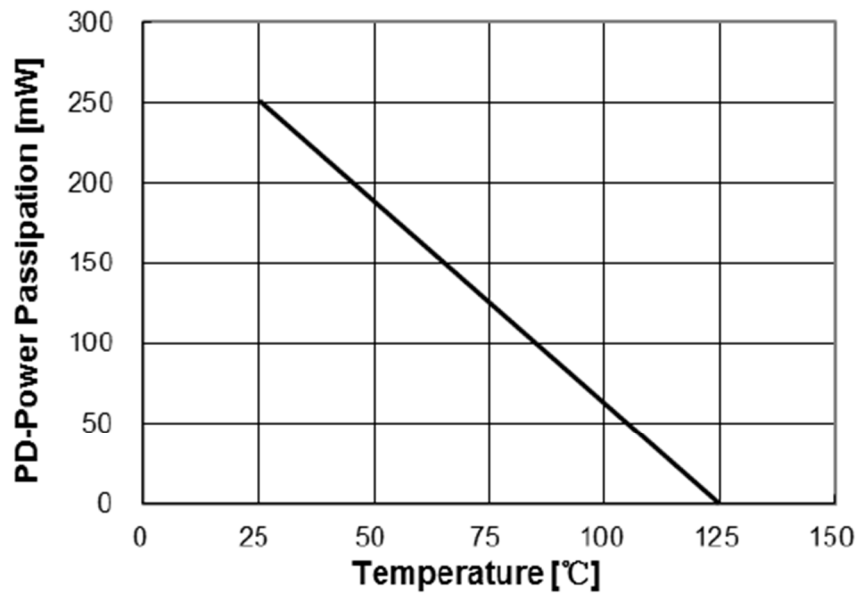
These ratings are limiting values above which the serviceability of the diode may be impaired.

Electrical Characteristics

TA = 25°C unless otherwise noted

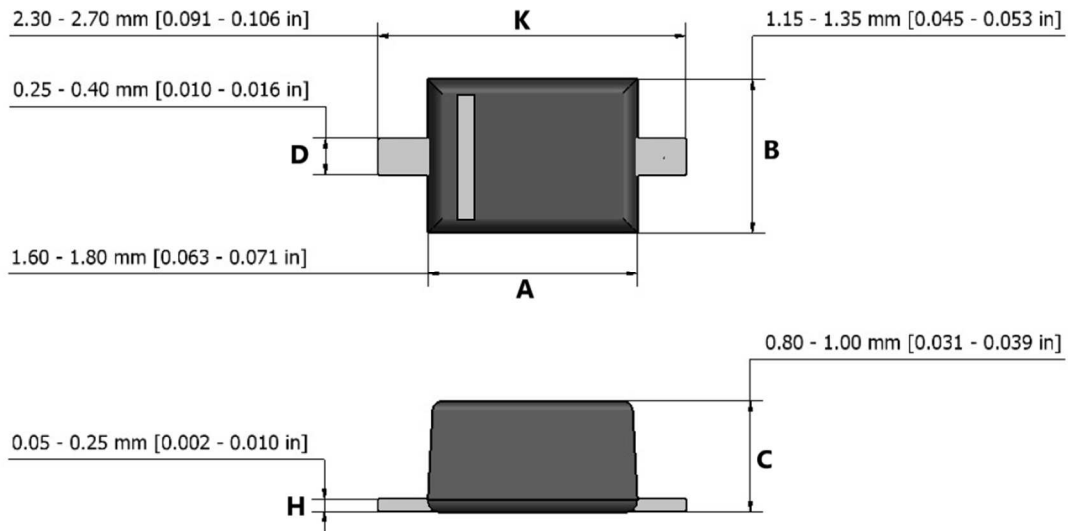
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _{BR}	Reverse Breakdown Voltage	I _R =1mA	40			V
I _R	Reverse Leakage Current	V _R =40V	-	-	1	mA
V _F	Forward Voltage	I _F =1A	-	-	0.60	V
C _d	Diode Capacitance	V _R =4V, f=1MHZ	-	30	-	pF

Typical Characteristics



Package Dimension

SOD-323



NOTES:

1. The above package outline is similar to JEITA SC-90.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.6	1.8	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.8	1	0.031	0.039
D	0.25	0.4	0.01	0.016
H	0.05	0.25	0.002	0.01
K	2.3	2.7	0.091	0.106





Pin 1.CATHODE
Pin 2.ANODE

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